NTR4101P

Trench Power MOSFET
−20 V, Single P−Channel, SOT−23

Features

- Leading −20 V Trench for Low $R_{DS(on)}$
- −1.8 V Rated for Low Voltage Gate Drive
- SOT−23 Surface Mount for Small Footprint
- Pb−Free Package is Available

Applications

- Load/Power Management for Portables
- Load/Power Management for Computing
- Charging Circuits and Battery Protection

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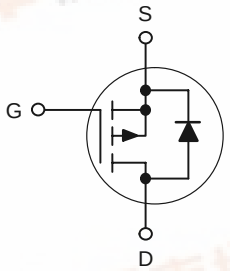
$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	I_D MAX
−20 V	70 mΩ @ −4.5 V	−3.2 A
	90 mΩ @ −2.5 V	
	112 mΩ @ −1.8 V	

P−Channel MOSFET

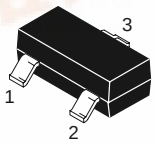


MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

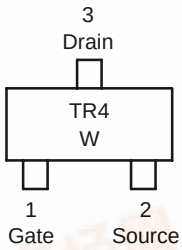
Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−20	V
Gate−to−Source Voltage			V_{GS}	±8.0	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−2.4	A
		T_A = 85°C		−1.7	
	t ≤ 10 s	T_A = 25°C		−3.2	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	0.73	W
	t ≤ 10 s			1.25	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	−1.8	A
		T_A = 85°C		−1.3	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.42	W
Pulsed Drain Current	tp = 10 μs		I_{DM}	−7.5	A
ESD Capability (Note 3)	C = 100 pF, RS = 1500 Ω		ESD	225	V
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−2.4	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

MARKING DIAGRAM & PIN ASSIGNMENT



SOT−23
CASE 318
STYLE 21



TR4 = Device Code
W = Work Week

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	170	°C/W
Junction−to−Ambient − t < 10 s (Note 1)	$R_{\theta JA}$	100	
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	300	

1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
2. Surface−mounted on FR4 board using the minimum recommended pad size.
3. ESD Rating Information: HBM Class 0

ORDERING INFORMATION

Device	Package	Shipping†
NTR4101PT1	SOT−23	3000/Tape & Reel
NTR4101PT1G	SOT−23 Pb−Free	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage (Note 4) (V_{GS} = 0 V, I_D = −250 μA)		$V_{(BR)DSS}$	−20			V
Zero Gate Voltage Drain Current (Note 4) (V_{GS} = 0 V, V_{DS} = −16 V)		I_{DSS}			−1.0	μA
Gate−to−Source Leakage Current (V_{GS} = ±8.0 V, V_{DS} = 0 V)		I_{GSS}			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage (Note 4) (V_{GS} = V_{DS}, I_D = −250 μA)		$V_{GS(th)}$	−0.40	−0.720	−1.5	V
Drain−to−Source On−Resistance (V_{GS} = −4.5 V, I_D = −1.6 A) (V_{GS} = −2.5 V, I_D = −1.3 A) (V_{GS} = −1.8 V, I_D = −0.9 A)		$R_{DS(on)}$		 70 90 112	 85 120 210	mΩ
Forward Transconductance (V_{DS} = −5.0 V, I_D = −2.3 A)		g_{FS}		75		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	(V_{GS} = 0 V, f = 1 MHz, V_{DS} = −10 V)	C_{iss}		675		pF
Output Capacitance		C_{oss}		100		
Reverse Transfer Capacitance		C_{rss}		75		
Total Gate Charge	(V_{GS} = −4.5 V, V_{DS} = −10 V, I_D = −1.6 A)	$Q_{G(tot)}$		7.5	8.5	nC
Gate−to−Source Gate Charge	(V_{DS} = −10 V, I_D = −1.6 A)	Q_{GS}		1.2		nC
Gate−to−Drain “Miller” Charge	(V_{DS} = −10 V, I_D = −1.6 A)	Q_{GD}		2.2		nC
Gate Resistance		R_G		6.5		Ω
SWITCHING CHARACTERISTICS (Note 5)						
Turn−On Delay Time	(V_{GS} = −4.5 V, V_{DS} = −10 V, I_D = −1.6 A, R_G = 6.0 Ω)	$t_{d(on)}$		7.5		ns
Rise Time		t_r		12.6		
Turn−Off Delay Time		$t_{d(off)}$		30.2		
Fall Time		t_f		21.0		
DRAIN−SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	(V_{GS} = 0 V, I_S = −2.4 A)	V_{SD}		−0.82	−1.2	V
Reverse Recovery Time	(V_{GS} = 0 V, dI_{SD}/dt = 100 A/μs, I_S = −1.6 A)	t_{rr}		12.8	15	ns
Charge Time		t_a		9.9		ns
Discharge Time		t_b		3.0		ns
Reverse Recovery Charge		Q_{rr}		1008		nC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperature.

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

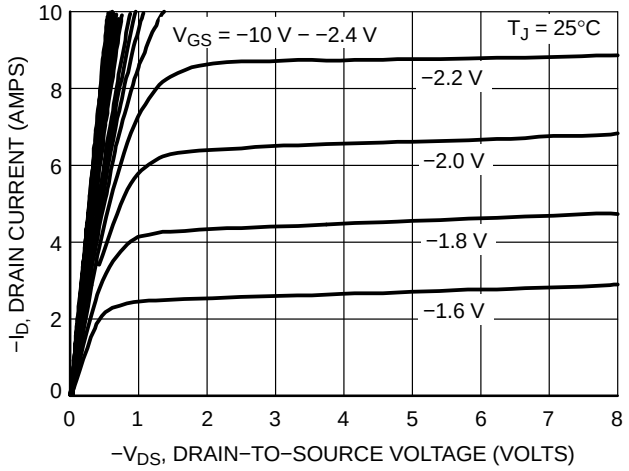


Figure 1. On−Region Characteristics

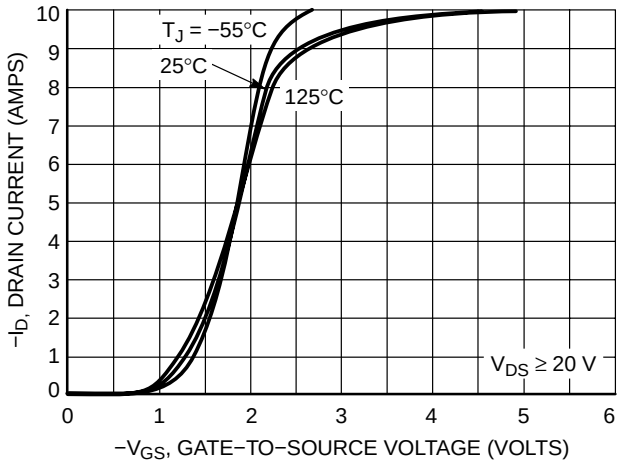


Figure 2. Transfer Characteristics

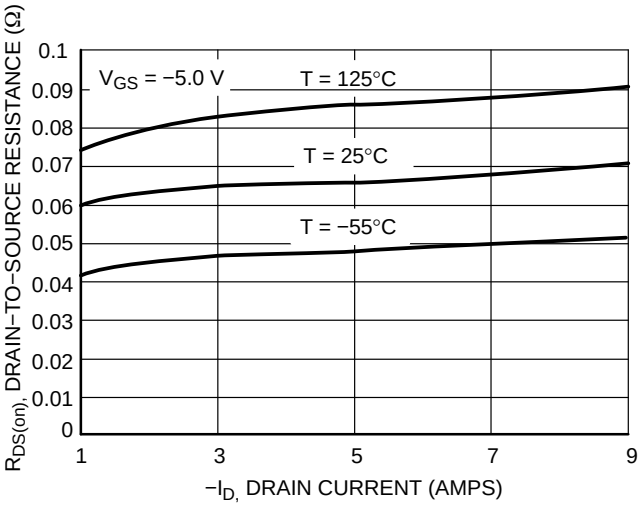


Figure 3. On−Resistance vs. Drain Current and Temperature

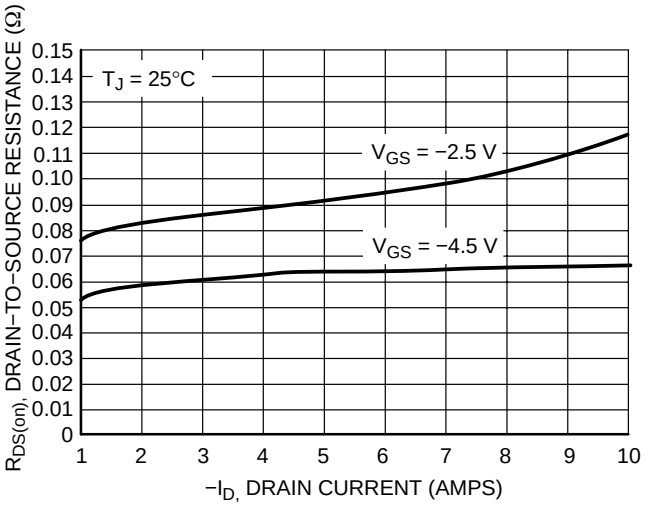


Figure 4. On−Resistance vs. Drain Current and Temperature

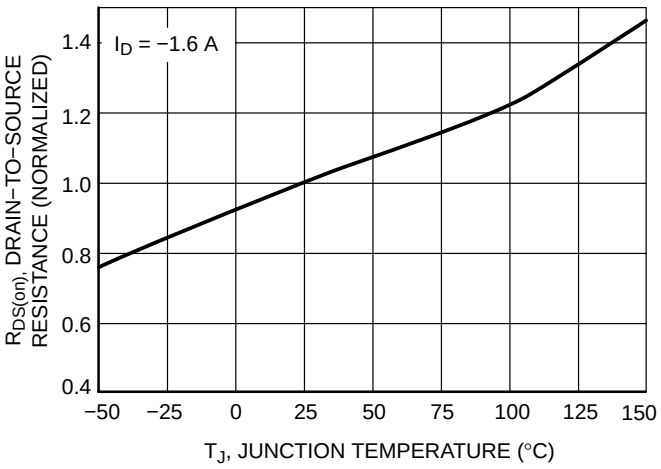


Figure 5. On−Resistance Variation with Temperature

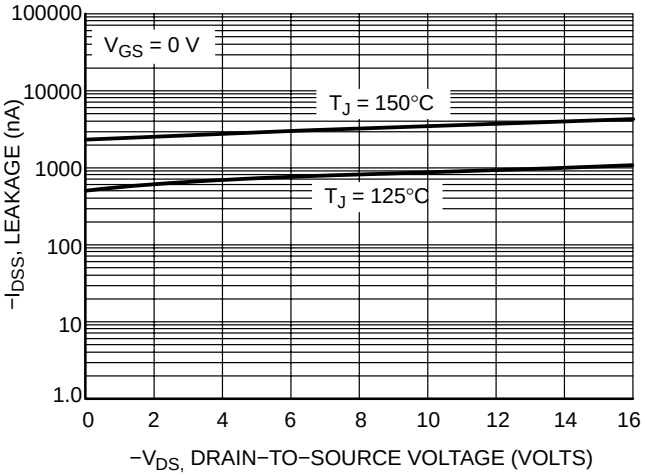


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

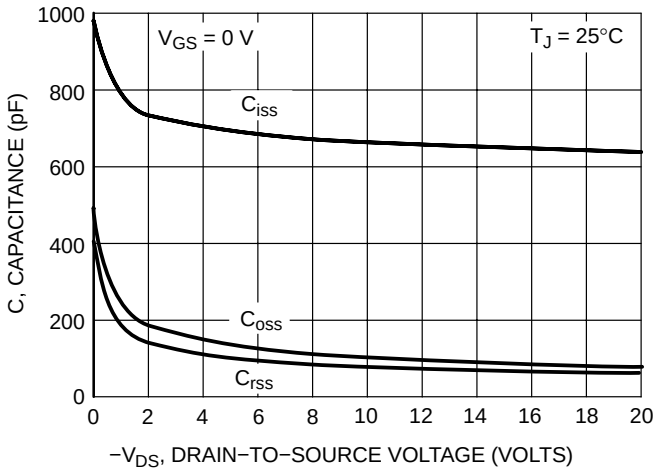


Figure 7. Capacitance Variation

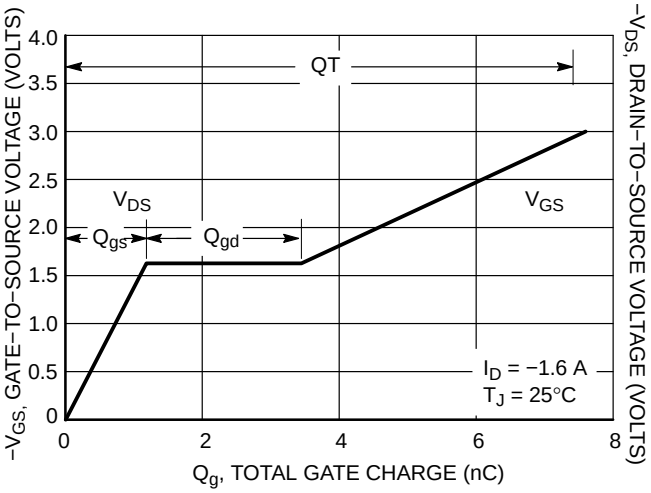


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Gate Charge

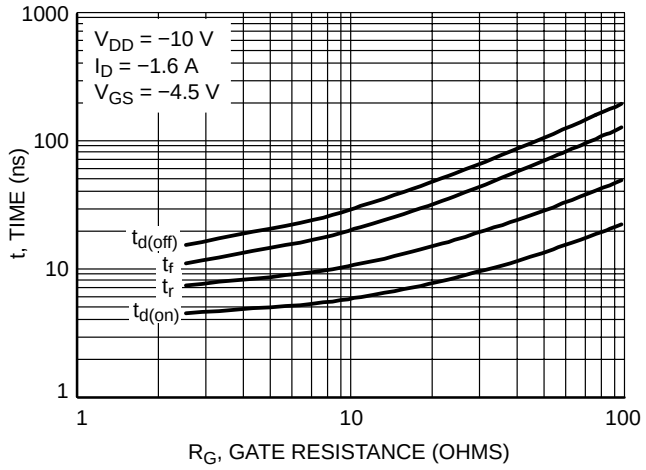


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

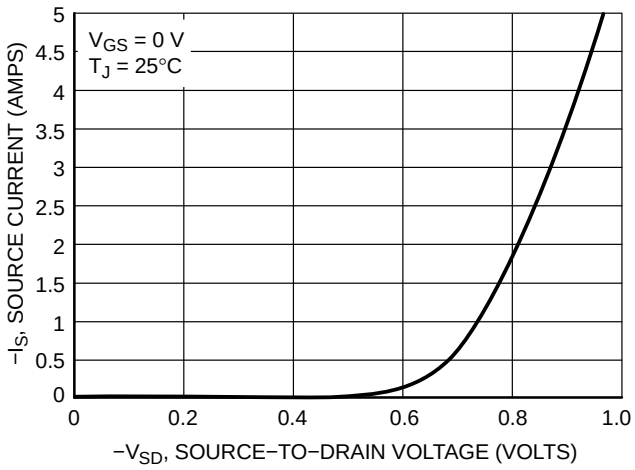
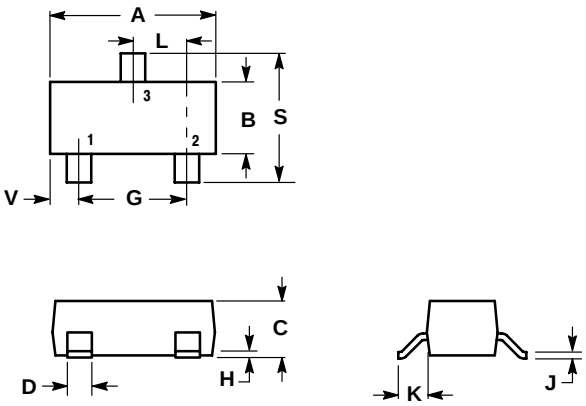


Figure 10. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AK

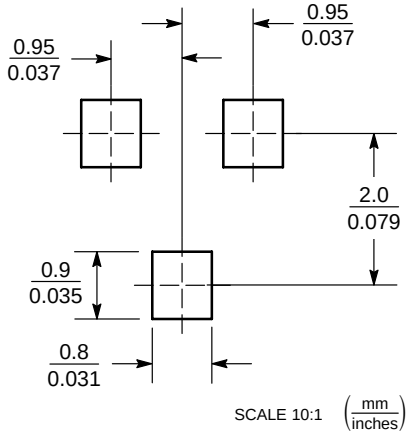


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−03 AND −07 OBSOLETE, NEW STANDARD 318−08.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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